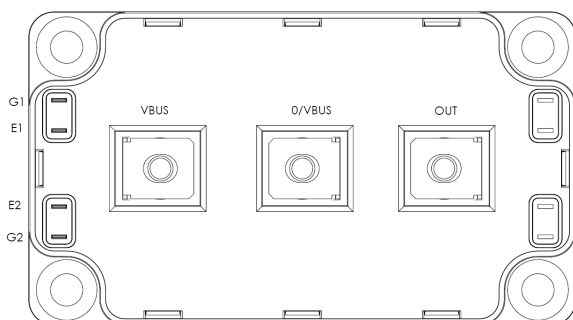
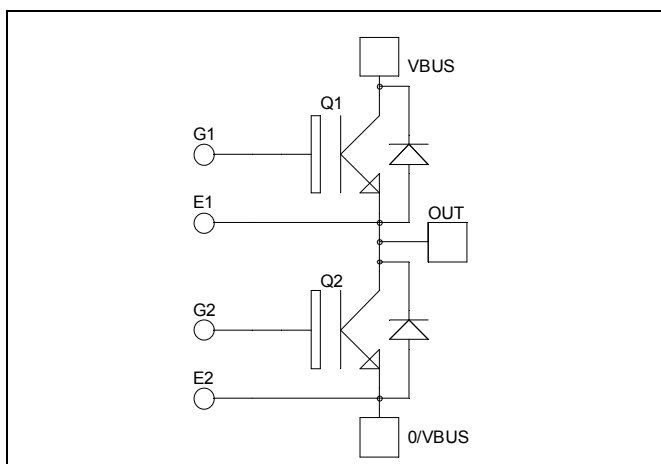


*Phase leg  
Fast Trench + Field Stop IGBT3  
Power Module*

**$V_{CES} = 1200V$   
 $I_C = 400A @ T_c = 80^\circ C$**



## Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

## Features

- Fast Trench + Field Stop IGBT3 Technology
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 20 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
  - Symmetrical design
  - M5 power connectors
- High level of integration

## Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile
- RoHS Compliant

## Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
$V_{CES}$	Collector - Emitter Breakdown Voltage	1200	V
$I_C$	Continuous Collector Current	$T_c = 25^\circ C$	560 *
		$T_c = 80^\circ C$	400
$I_{CM}$	Pulsed Collector Current	$T_c = 25^\circ C$	800
$V_{GE}$	Gate - Emitter Voltage	$\pm 20$	V
$P_D$	Maximum Power Dissipation	$T_c = 25^\circ C$	1785
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^\circ C$	800A @ 1100V

\* Specification of IGBT device but output current must be limited to 500A to not exceed a delta of temperature greater than 100°C for the connectors.

**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on [www.microsemi.com](http://www.microsemi.com)

**All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified**

**Electrical Characteristics**

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>	<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$			750	$\mu A$
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	$V_{GE} = 15V$ $I_C = 400A$	$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	1.4 2.0	2.1	V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 4mA$	5.0	5.8	6.5	V
$I_{GES}$	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$			600	nA

**Dynamic Characteristics**

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>	<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
$C_{ies}$	Input Capacitance	$V_{GE} = 0V$		28		nF
$C_{oes}$	Output Capacitance	$V_{CE} = 25V$		1.6		
$C_{res}$	Reverse Transfer Capacitance	$f = 1MHz$		1.2		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching ( $25^\circ\text{C}$ ) $V_{GE} = \pm 15V$ $V_{Bus} = 600V$ $I_C = 400A$ $R_G = 1.2\Omega$		260		ns
$T_r$	Rise Time			30		
$T_{d(off)}$	Turn-off Delay Time			420		
$T_f$	Fall Time			80		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching ( $125^\circ\text{C}$ ) $V_{GE} = \pm 15V$ $V_{Bus} = 600V$ $I_C = 400A$ $R_G = 1.2\Omega$		290		ns
$T_r$	Rise Time			50		
$T_{d(off)}$	Turn-off Delay Time			520		
$T_f$	Fall Time			100		
$E_{on}$	Turn on Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 600V$ $I_C = 400A$ $R_G = 1.2\Omega$	$T_j = 125^\circ\text{C}$	40		mJ
$E_{off}$	Turn off Energy		$T_j = 125^\circ\text{C}$	40		

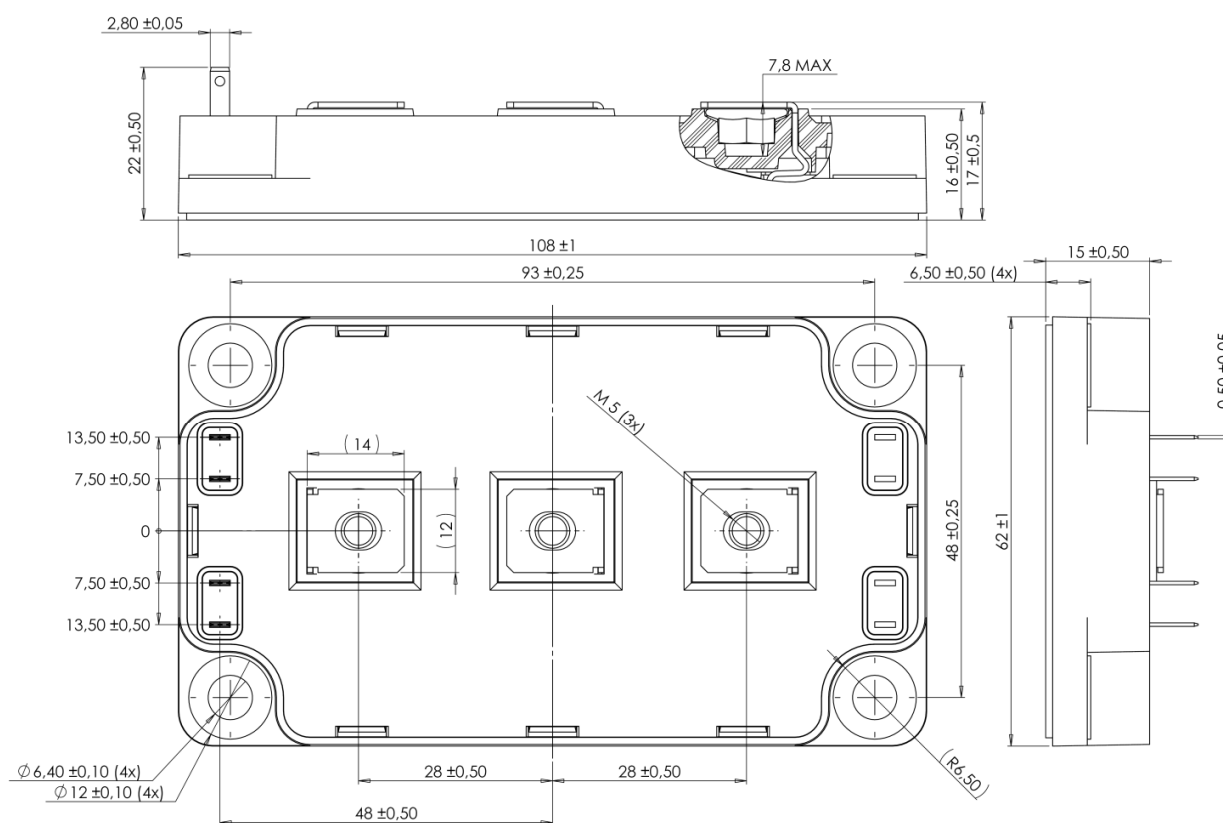
**Reverse diode ratings and characteristics**

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>	<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage		1200			V
$I_{RM}$	Maximum Reverse Leakage Current	$V_R = 1200V$	$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$		700 900	$\mu A$
$I_F$	DC Forward Current		$T_c = 80^\circ\text{C}$	400		A
$V_F$	Diode Forward Voltage	$I_F = 400A$ $V_{GE} = 0V$	$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	1.6 1.6	2.1	V
$t_{rr}$	Reverse Recovery Time	$I_F = 400A$ $V_R = 600V$ $di/dt = 4000A/\mu s$	$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	170 280		ns
$Q_{rr}$	Reverse Recovery Charge		$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	36 72		
$E_r$	Reverse Recovery Energy		$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	20 36		mJ

## Thermal and package characteristics

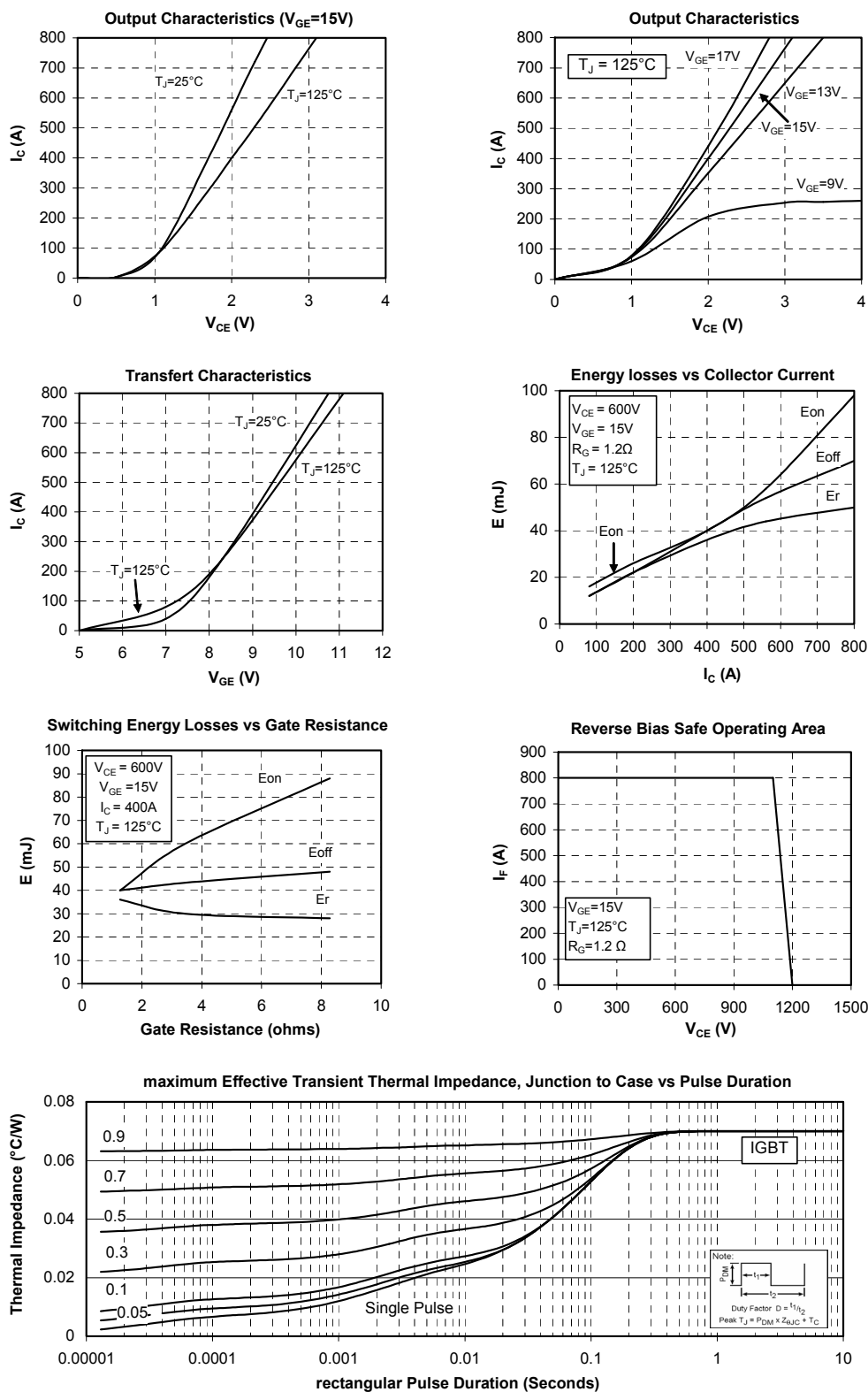
<i>Symbol</i>	<i>Characteristic</i>			<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
R <sub>thJC</sub>	Junction to Case Thermal Resistance		IGBT			0.07	°C/W
			Diode			0.13	
V <sub>ISOL</sub>	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T <sub>J</sub>	Operating junction temperature range			-40		150	°C
T <sub>STG</sub>	Storage Temperature Range			-40		125	
T <sub>C</sub>	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M6	3		5	N.m
		For terminals	M5	2		3.5	
Wt	Package Weight					300	g

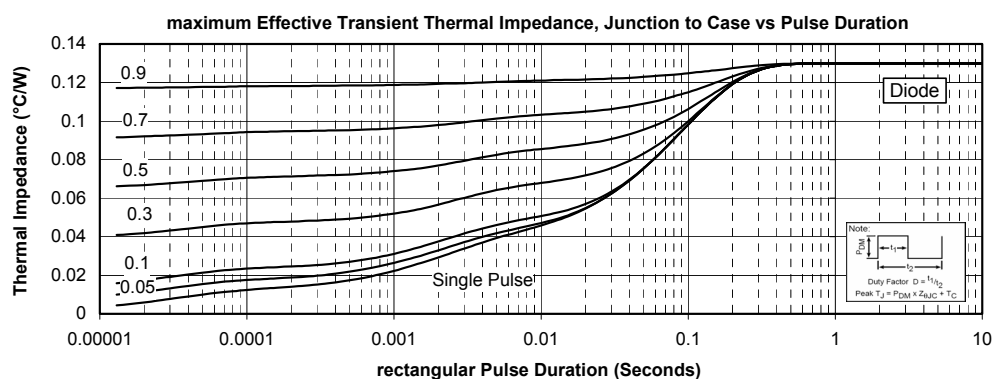
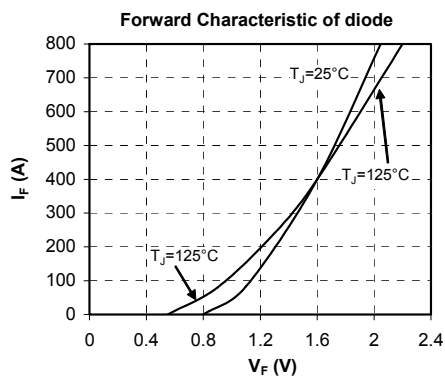
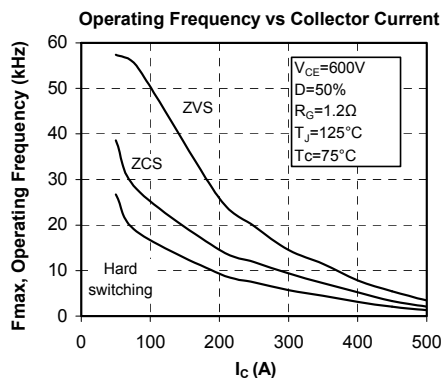
### SP6 Package outline (dimensions in mm)



See application note APT0601 - Mounting Instructions for SP6 Power Modules on [www.microsemi.com](http://www.microsemi.com)

## Typical Performance Curve





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